



ON Semiconductor®

FDN359AN N-Channel Logic Level PowerTrench™ MOSFET

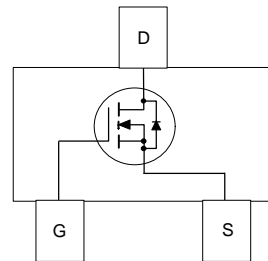
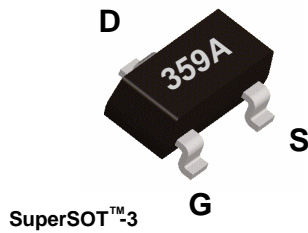
General Description

This N-Channel Logic Level MOSFET is produced using ON Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

Features

- 2.7 A, 30 V. $R_{DS(ON)} = 0.046 \Omega @ V_{GS} = 10 \text{ V}$
 $R_{DS(ON)} = 0.060 \Omega @ V_{GS} = 4.5 \text{ V}$.
- Very fast switching.
- Low gate charge (5nC typical).
- High power version of industry standard SOT-23 package. Identical pin out to SOT-23 with 30% higher power handling capability.



Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Maximum Drain Current - Continuous (Note 1a)	2.7	A
	- Pulsed	15	
P_D	Maximum Power Dissipation (Note 1a) (Note 1b)	0.5	W
		0.46	
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to 150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	250	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	75	$^\circ\text{C/W}$

Electrical Characteristics (T_A = 25 °C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	30			V
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	I _D = 250 μA, Referenced to 25 °C		23		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V			1	μA
		T _J = 55°C			10	μA
I _{GSSF}	Gate - Body Leakage, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate - Body Leakage, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA
ON CHARACTERISTICS (Note)						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	1	1.6	3	V
ΔV _{GS(th)} /ΔT _J	Gate Threshold Voltage Temp. Coefficient	I _D = 250 μA, Referenced to 25 °C		-4		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 2.7 A		0.037	0.046	Ω
		T _J = 125°C		0.055	0.075	
		V _{GS} = 4.5 V, I _D = 2.4 A		0.049	0.06	
I _{D(on)}	On-State Drain Current	V _{GS} = 10 V, V _{DS} = 5 V	15			A
g _{FS}	Forward Transconductance	V _{DS} = 5 V, I _D = 2.7 A		9.5		S
DYNAMIC CHARACTERISTICS						
C _{iss}	Input Capacitance	V _{DS} = 10 V, V _{GS} = 0 V, f = 1.0 MHz		480		pF
C _{oss}	Output Capacitance			120		pF
C _{rss}	Reverse Transfer Capacitance			45		pF
SWITCHING CHARACTERISTICS (Note)						
t _{D(on)}	Turn - On Delay Time	V _{DD} = 5 V, I _D = 1 A, V _{GS} = 4.5 V, R _{GEN} = 6 Ω		6	12	ns
t _r	Turn - On Rise Time			13	24	ns
t _{D(off)}	Turn - Off Delay Time			15	27	ns
t _f	Turn - Off Fall Time			4	10	ns
Q _g	Total Gate Charge	V _{DS} = 10 V, I _D = 2.7 A, V _{GS} = 5 V		5	7	nC
Q _{gs}	Gate-Source Charge			1.4		nC
Q _{gd}	Gate-Drain Charge			1.6		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I _S	Maximum Continuous Drain-Source Diode Forward Current				0.42	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 0.42 A (Note)		0.65	1.2	V

Note:

- R_{th(j-c)} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{th(j-c)} is guaranteed by design while R_{th(c-a)} is determined by the user's board design.

Typical R_{th(j-c)} using the board layouts shown below on FR-4 PCB in a still air environment :



a. 250°C/W when mounted on a 0.02 in² pad of 2oz Cu.



b. 270°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%.

Typical Electrical Characteristics

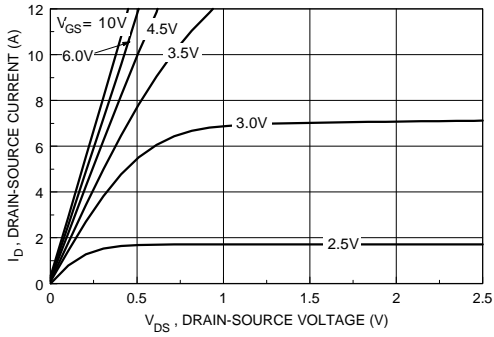


Figure 1. On-Region Characteristics.

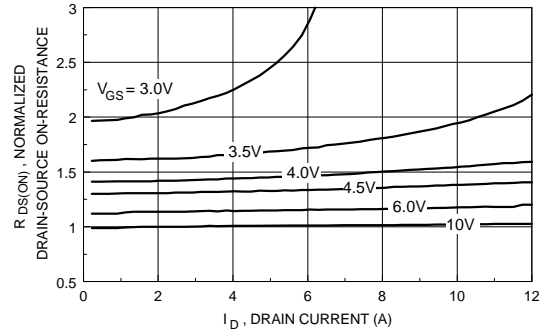


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

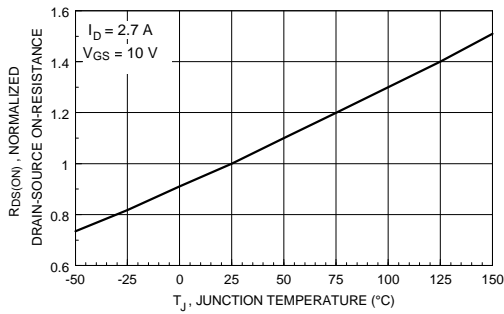


Figure 3. On-Resistance Variation with Temperature.

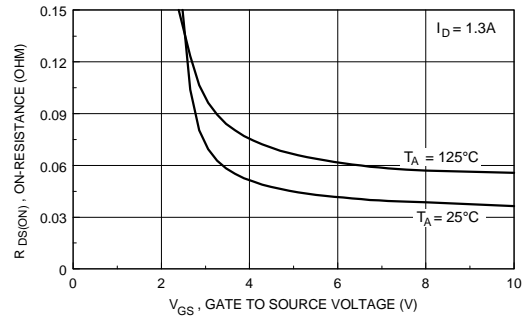


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

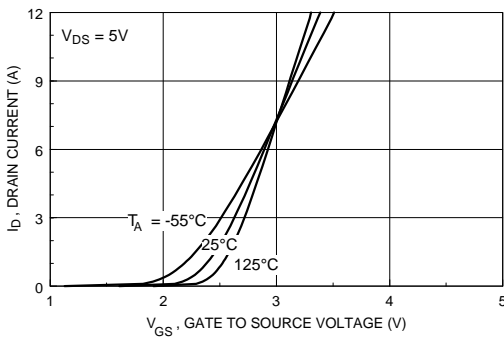


Figure 5. Transfer Characteristics.

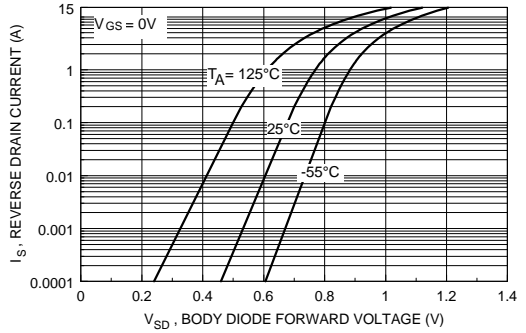


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Electrical Characteristics

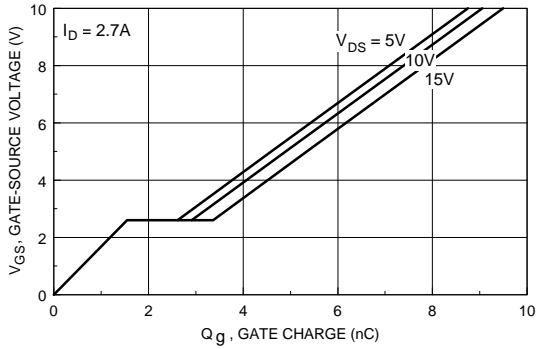


Figure 7. Gate Charge Characteristics.

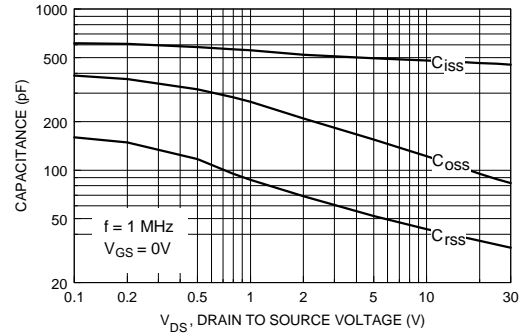


Figure 8. Capacitance Characteristics.

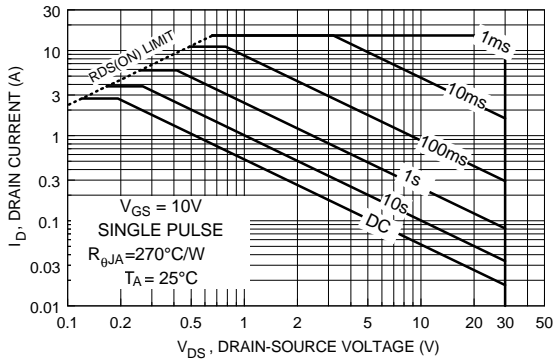


Figure 9. Maximum Safe Operating Area.

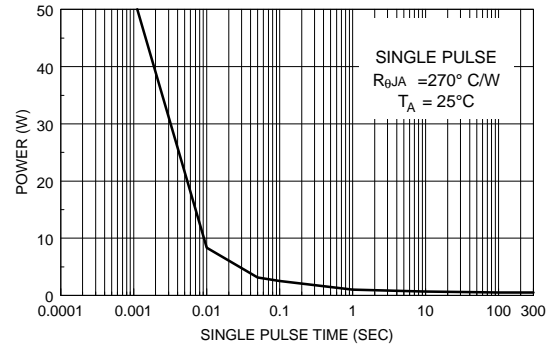


Figure 10. Single Pulse Maximum Power Dissipation.

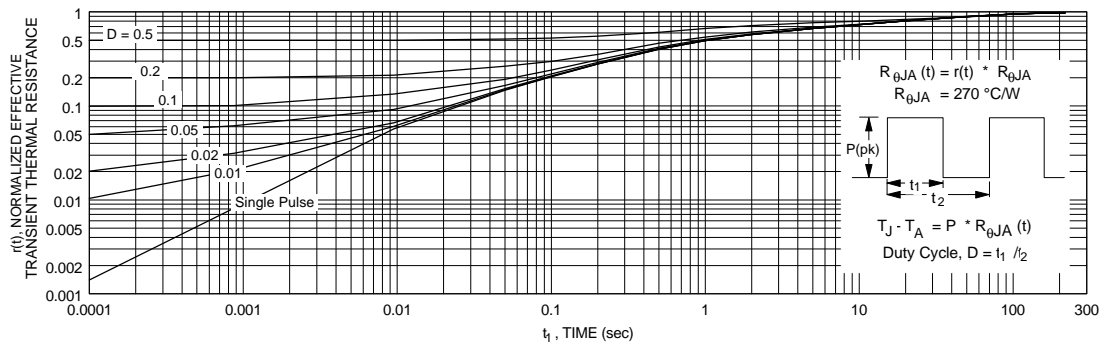


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in note 1b.
Transient thermal response will change depending on the circuit board design.

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